

BSS100 / BSS123

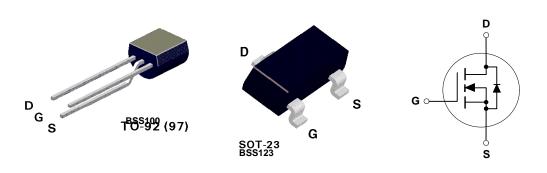
N-Channel Logic Level Enhancement Mode Field Effect Transistor

General Description

These N-Channel logic level enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process has been especially tailored to minimize on-state resistance, provide superior switching performance. This product is particularly suited to low voltage, low current applications, such as small servo motor controls, power MOSFET gate drivers, and other switching applications.

Features

- BSS100: 0.22A, 100V. $R_{DS(ON)} = 6\Omega$ @ $V_{GS} = 10V$. BSS123: 0.17A, 100V. $R_{DS(ON)} = 6\Omega$ @ $V_{GS} = 10V$
- High density cell design for extremely low R_{DS(ON)}.
- Voltage controlled small signal switch.
- Rugged and reliable.



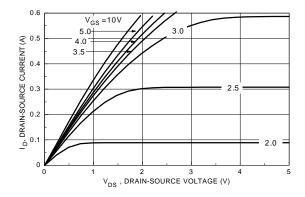
Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	BSS100	BSS123	Units
V _{DSS}	Drain-Source Voltage	1	V	
V_{DGR}	Drain-Gate Voltage ($R_{GS} \le 20K\Omega$)	1	00	V
V_{GSS}	Gate-Source Voltage - Continuous	±	: 14	V
	- Non Repetitive ($T_P < 50 \mu S$)	±	:20	
I _D	Drain Current - Continuous	0.22	0.17	А
	- Pulsed	0.9	0.68	
P_{D}	Total Power Dissipation @ T _A = 25°C	0.63	0.36	W
T_J , T_{STG}	Operating and Storage Temperature Range	-55	℃	
T _L	Maximum Lead Temperature for Soldering Purposes, 1/16" from Case for 10 Seconds	3	℃	
THERMA	L CHARACTERISTICS			
$R_{\theta JA}$	Thermal Resistacne, Junction-to-Ambient	200	350	°C/W

Symbol	Parameter	Type	Min	Тур	Max	Units	
OFF CHA	RACTERISTICS				ı		.1
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	All	100			V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$	BSS100			15	μΑ
		$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$	BSS123			1	μA
		$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$ $T_{J} = 125^{\circ}\text{C}$	All			60	μA
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$	BSS100			10	nA
		$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$	BSS123			10	nA
I _{GSSF}	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$	BSS100			10	nA
		$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$	BSS123			50	nA
ON CHAR	ACTERISTICS (Note 1)	·	•		•		•
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 1 \text{ mA}$	All	0.8	1.4	2	V
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_{D} = 0.22 \text{ A}$	BSS100		2.8	6	Ω
. ,		$V_{GS} = 10 \text{ V}, I_{D} = 0.17 \text{ A}$	BSS123		2.8	6	
		$V_{GS} = 4.5 \text{ V}, I_{D} = 0.22 \text{ A}$	BSS100		3.2	10	
		$V_{GS} = 4.5 \text{ V}, I_{D} = 0.17 \text{ A}$	BSS123		3.2	10	
g _{FS}	Forward Transconductance	$V_{DS} = 10 \text{ V}, I_{D} = 0.22 \text{ A}$	BSS100	80.0	0.4		S
		$V_{DS} = 10 \text{ V}, I_{D} = 0.17 \text{ A}$	BSS123	0.08	0.4]
DYNAMIC	CHARACTERISTICS	·	•		•		•
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, \ V_{GS} = 0 \text{ V}, $ $f = 1.0 \text{ MHz}$	All		29	60	pF
C _{oss}	Output Capacitance	f = 1.0 MHz	All		10	15	pF
C _{rss}	Reverse Transfer Capacitance		All		2	6	pF
SWITCHIN	IG CHARACTERISTICS (Note 1)		•		3	•	-
t _{D(on)}	Turn - On Delay Time	$V_{DD} = 30 \text{ V}, \ I_{D} = 0.28 \text{ A},$	All			8	ns
t _r	Turn - On Rise Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 50 \Omega$	All			8	ns
$\mathbf{t}_{D(off)}$	Turn - Off Delay Time		All			13	ns
t _f	Turn - Off Fall Time		All			16	ns
Q_g	Totall Gate Charge	$V_{DS} = 10 \text{ V}, I_{D} = 0.22 \text{ A},$	All		1.4	2	nC
Q_{gs}	Gate-Source Charge	$V_{GS} = 10 \text{ V},$	All		0.15	0.25	nC
Q_{gd}	Gate-Drain Charge		All		0.2	0.4	nC
DRAIN-SO	DURCE DIODE CHARACTERISTICS AND I	MAXIMUM RATINGS					
Is	Maximum Continuous Source Current	BSS100			0.22	Α	
			BSS123			0.17	
$I_{\rm SM}$	Maximum Pulse Source Current (Note 1)		BSS100			0.9	Α
			BSS123			0.68	
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, \ I_{S} = 0.44 \text{ A}$	BSS100		0.9	1.3	V
		$V_{GS} = 0 \text{ V}, I_{S} = 0.34 \text{ A}$	BSS123		0.9	1.3	

Note: 1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

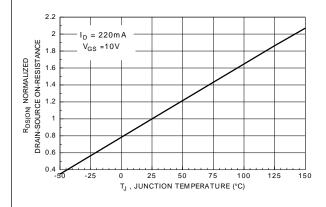
Typical Electrical Characteristics



2.4 V_{GS} = 2.5V V_{GS} = 2.5V V_{GS} = 2.5V 3.0 3.5 3.5 3.5 1.0 0.1 0.2 0.3 0.4 0.5 0.6 1.0 0.5 0.6

Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.



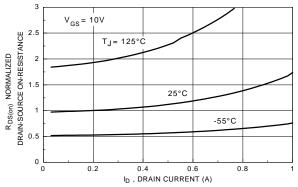
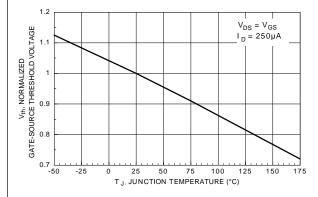


Figure 3. On-Resistance Variation with Temperature.

Figure 4. On-Resistance Variation with Drain Current and Temperature.



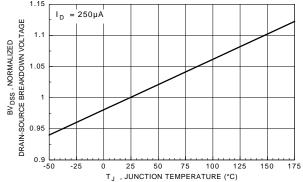


Figure 5. Gate Threshold Variation with Temperature.

Figure 6. Breakdown Voltage Variation with Temperature.

Typical Electrical Characteristics (continued)

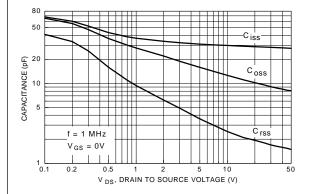


Figure 7. Capacitance Characteristics.

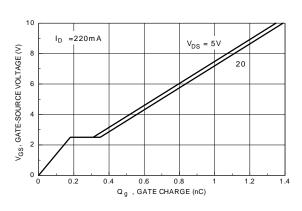


Figure 8. Gate Charge Characteristics.

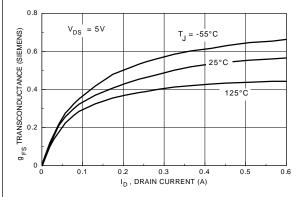


Figure 9. Transconductance Variation with Drain Current and Temperature.

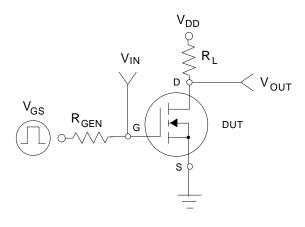


Figure 10. Switching Test Circuit.

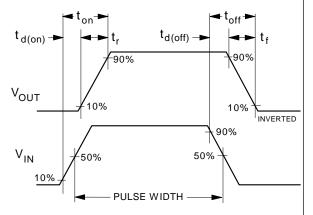
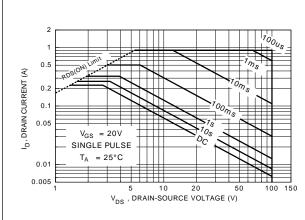


Figure 11. Switching Waveforms.



0.5 0.5 0.5 0.05 0.05 0.0

Figure 12. BSS100 Maximum Safe Operating Area.

Figure 13. BSS123 Maximum Safe Operating Area.

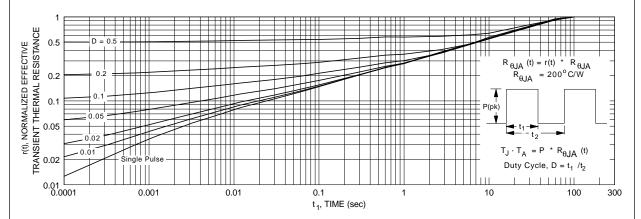


Figure 14. BSS100 Transient Thermal Response Curve.

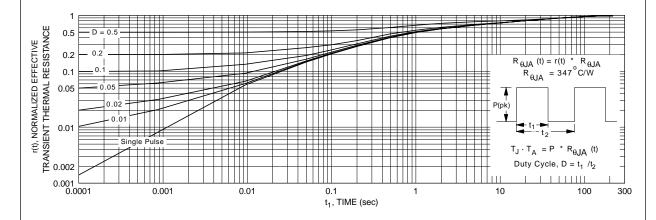


Figure 15. BSS123 Transient Thermal Response Curve.

TO-92 Tape and Reel Data FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVK//418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: Label 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z Е 2,000 D27Z Ammo М 2,000 D74Z D75Z 2,000 **FSCINT** Unit weight = 0.22 gm Reel weight with components = 1.04 kg Ammo weight with components = 1.02 kg Max quantity per intermediate box = 10,000 units Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD 2.0 K / BOX Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** NO EOL TO-92 STANDARD STRAIGHT FOR: PKG 92, NO LEADCLIP 2.0 K / BOX 94 (NON PROELECTRON SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)



Style "A", D26Z, D70Z (s/h)

Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0



FIRST WIRE OFF IS EMITTER (ON PKG. 92) ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON BOTTOM



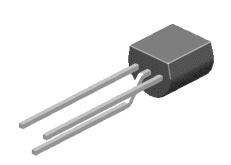
FIRST WIRE OFF IS COLLECTOR (ON PKG. 92) ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP

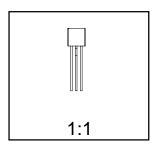


TO-92 Package Dimensions



TO-92; TO-18 Reverse Lead Form (J35Z Option) (FS PKG Code 92, 94, 96)

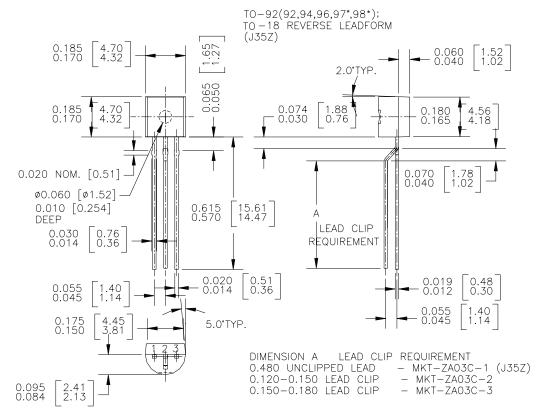




Scale 1:1 on letter size paper

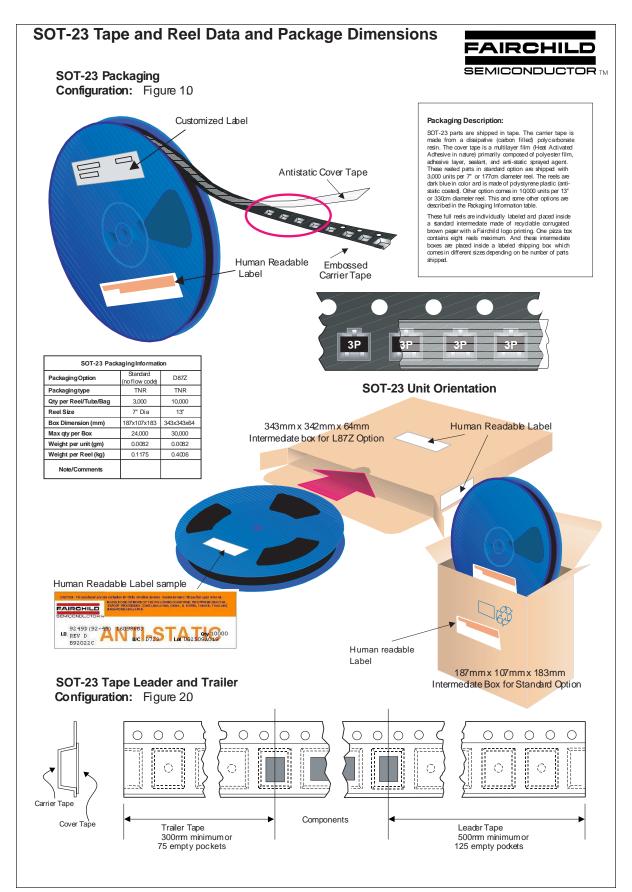
Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.22



Note: All package 97 or 98 transistors are leadformed to this configuration prior to bulk shipment. Order L34Z option if in-line leads are preferred on package 97 or 98.

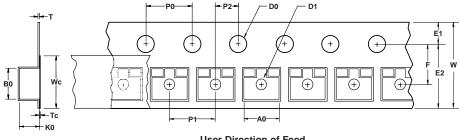
^{*} Standard Option on 97 & 98 package code



SOT-23 Tape and Reel Data and Package Dimensions, continued

SOT-23 Embossed Carrier Tape

Configuration: Figure 3.0



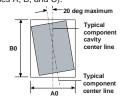
User Direction of Feed	

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



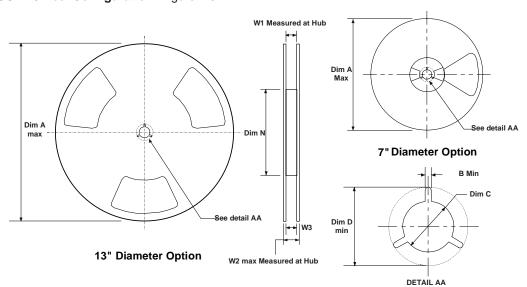
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

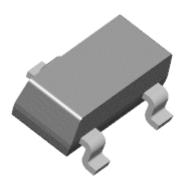
SOT-23 Reel Configuration: Figure 4.0

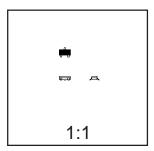


	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

SOT-23 Tape and Reel Data and Package Dimensions, continued

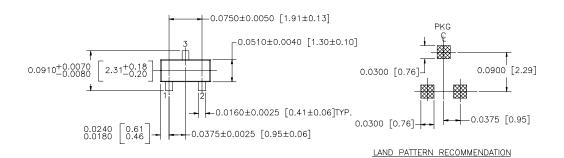
SOT-23 (FS PKG Code 49)

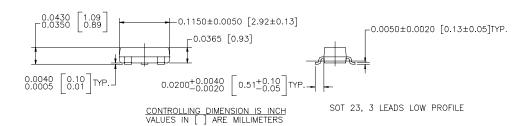




Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082





NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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